A method of simulating operation of a VLSI interconnect structure having capacitive and inductive coupling between nodes thereof. A matrix X and a matrix Y containing different combinations of passive circuit element values for the interconnect structure are obtained where the element values for each matrix include inductance L and inverse capacitance 1/P.

Numerical integration is used to solve first and second equations, each including as a factor the product of the inverse matrix $X^{-1}$ and at least one other matrix, with first equation including $X^{-1}Y$, $X^{-1}A$, and $X^{-1}P$, and the second equation including $X^{-1}A$ and $X^{-1}P$.

9 Claims, 17 Drawing Sheets
OTHER PUBLICATIONS


* cited by examiner